

#2

Form PTO-1449	LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use Several Sheets if Necessary)	ATTY. DOCKET NO.	SERIAL NO.
		JG00069	09/766046
		Ramdani et al.	
		FILING DATE	GROUP
		01/19/01	2811

JF945 U.S. PTO
09/766046
01/19/01

REFERENCE DESIGNATION

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	ISSUE DATE	NAME	CLASS	SUBCLASS	FILING DATE
<i>SKH</i>	AA	5 2 7 0 2 9 8	12/14-93	Ramesh	505	1	8/4/92
	AB	5 4 1 8 3 8 9	5/23/95	Watanabe	257	295	11/9/93
	AC	5 2 4 8 5 6 4	9/28/93	Ramesh	428	688	12/9/92
	AD	5 1 5 5 6 5 8	10/13/92	Inam et al.	361	321	3/5/92
	AE	6 0 5 5 1 7 9	4/25/00	Koganei et al.	365	158	5/17/99
	AF	5 3 2 6 7 2 1	7/5/94	Summerfelt	437	131	5/1/92
	AG	5 3 1 0 7 0 7	5/10/94	Oishi et al.	501	126	9/28/92
	AH	4 9 9 9 8 4 2	3/12/91	Huang et al.	372	45	3/1/89
	AI	5 8 7 4 8 6 0	2/23/99	Brunel et al.	330	285	12/4/96
	AJ	6 0 0 2 3 7 5	12/14/99	Corman et al.	343	853	9/2/97
	AK	4 8 8 2 3 0 0	11/21/89	Inoue et al.	437	236	10/6/88
	AL	5 6 7 4 3 6 6	10/7/97	Hayashi et al.	204	298.09	6/7/95
	AM	5 7 3 1 2 2 0	3/24/98	Tsu et al.	437	60	6/7/95
	AN	5 8 2 8 0 8 0	10/27/98	Yano et al.	257	43	8/17/95
<i>SKH</i>	AO	5 8 0 1 1 0 5	9/1/98	Yano et al.	438	785	6/14/96

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

<i>SKH</i>	AP	"Optimizing GMR Spin Valves: The Outlook for Improved Properties", W. F. Enghoff et al., 1998 Int'l NonVolatile Memory Technology Conference, pp. 34-37.
	AQ	"Processing and Performance of Piezoelectric Films", Y. Wang et al., Univ. of MD, Wilcoxon Research Co., and Motorola Labs.
	AP	"Nonlinear acoustoelectric interactions in GaAs/LiNbO ₃ structures", M. Rotter et al., 1999 American Institute of Physics, pp. 965-967.
	AS	"Surface acoustic wave propagation on lead zirconate titanate thin films", K. Sreenivas et al., App. Phys. Lett. 52(9), 29 February 1988, pp. 709-711.
	AT	"Single Chip fused hybrids for acousto-electric and acousto-optic applications", M. Rotter et al., 1997 American Institute of Physics, pp. 2097-2099.
	AU	"Surface Acoustic Wave Propagation in PZT/YBCO/SrTiO ₃ and PbTi O ₃ /YBCO/SrTiO ₃ Epitaxial Heterostructures", Dept. of Physics & Astrophysics, Univ. of Delhi, pp. 275-283.
<i>SKH</i>	AV	"Ferroelectric Field Effect Transistor Based on Epitaxial Perovskite Heterostructures", S. Mathews et al., American Association for the Advancement of Science, 1997, pp.238-240.

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DATE CONSIDERED

19 APRIL 2002

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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EXAMINER INITIAL		DOCUMENT NUMBER	ISSUE DATE	NAME	CLASS	SUBCLASS	FILING DATE
	AW	6 1 0 3 0 0 8	8/15/00	McKee et al.	117	2	7/30/98
	AX	5 2 2 5 0 3 1	7/6/93	McKee et al.	156	612	4/10/91
	AY						

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	GRANT DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION YES NO
	AZ 9 9 1 4 8 0 4	3/25/99	PCT	H01L	21/258	X

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

	BA	"Formation of Si Epi./MgO-Al ₂ O ₃ Epi./SiO ₂ /Si and Its Epitaxial Film Quality," Masao Mikami et al., Fundamental Research Laboratories and Microelectronics Laboratories, pp. 31-34.
	BB	"An Epitaxial Si/Insulator/Si Structure Prepared by Vacuum Deposition of CaF ₂ and Silicon," T. Asano et al., Graduate School of Science and Engineering, Tokyo Institute of Technology, pp. 143-151.
	BE	"Reaction and Regrowth Control of CeO ₂ on Si(111) Surface for the Silicon-On-Insulator Structure," T. Chikyow et al., Appl. Phys. Lett. 65(8), 22 August 1994, pp. 1030-1032.
	BD	"Epitaxial Growth of CeO ₂ (100) Films on Si(100) Substrates by Dual Ion Beams Reactive Sputtering," J.F. Kang et al., Solid State Communications, Vol. 108, No. 4, pp. 225-227.
	BE	"Vertical-Cavity Surface-Emitting Lasers Come of Age," Robert A. Morgan et al., SPIE, Vol. 2683, pp. 18-29.
	BF	"Technical Analysis of Qualcomm QCP-800 Portable Cellular Phone(Transmitter Circuitry)," Talus Corporation, Qualcomm QCP-800 Technical Analysis Report, December 10, 1996, pp. 5-8.
	BG	"Properties of GaAs Si Grown by Molecular Beam Epitaxy," R. Houdre et al., Solid State and Molecular Sciences, 1990, pp. 91-114.
	BH	"Gallium Arsenide and Other Compound Semiconductors on Silicon," S.F. Fang et al., J. Appl. Phys. 68(7), 1 October 1990, pp. R31-R58.

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